

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RE APPLICATION OF: Jeng H. Hwang et al.

§ GROUP ART UNIT: Unknown

SERIAL NO.: 09/747,667

EXAMINER: Unknown

FILED: December 22, 2000

FOR: PLASMA HEATING OF A SUBSTRATE WITH § Attorney Docket No.:

SUBSEQUENT HIGH TEMPERATURE ETCHING

AM-5256-2

Date: May 3, 2001

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)(3)

Hon. Commissioner for Patents Washington, DC 20231

Sir:

In accordance with 37 CFR § 1.97(b)(3), applicants hereby request consideration of this Information Disclosure Statement. This Information Disclosure Statement is being submitted prior to the receipt of a first Office Action in the subject application. Applicants are providing herewith a copy of each document cited on the attached Form PTO-1449.

CERTIFICATE OF MAILING UNDER 37 CFR 1.10

I hereby certify that this paper is being deposited with the U.S. Postal Service on the date shown below with sufficient postage as U.S. EXPRESS MAIL NO. ET156670463US in an envelope addressed to the: Commissioner for Patents, Box DD, Washington, DC 20231.

Date: May 3, 2001

Shirley L. Church, Reg. No. 31,858

The submission of this Information Disclosure Statement and Form PTO-1449 is not an admission that the art cited is "prior art" with respect to the present invention, nor is it a representation that no better art exists. Applicants hereby reserve the right to swear behind or otherwise disprove any alleged "prior" nature of any art cited should the facts support and the situation warrant such an action.

If the Examiner has any questions, he is respectfully requested to contact the undersigned attorney at the telephone number set forth below.

Respectfully submitted,

Shirley L. Church

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FORM PTO-1449
Equivalent)

U.S. Department of Commerce Patent and Trademark Office U.S. Application Serial No. 09/747,667

Atty. Docket No. AM-5256

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Jeng H. Hwang et al. Applicants

December 22, 2000 Filing Date

<u>1746</u> 1765 Group

U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue <u>Date</u>	Name	Class	Subclass	Filing Date If Appropriate
<u>5A</u>	5,186,718	02/16/93	Tepman et al.	29	25.01	
SA	5,789,320	08/04/98	Andricacos et al.	438	678	
SA	6,030,666	02/29/00	Lam et al.	427	539	
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SA	6,087,265	07/11/00	Hwang	438	706	

Examiner

Date Considered

9/4/02

Shamin Ahmed

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



FOREIGN PATENT DOCUMENTS

Document Number	Publication <u>Date</u>	Name	Class	Subclass	Translation If Appropriate
DD 142966	07/23/80	Schade et al.	C23C	15/00	Abstract
DD 285224	12/05/90	Geiler et al.	H01L	21/265	Abstract
JP 53109475	09/25/78	Hitachi Ltd.	H01L	21/203	Abstract
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)



Chow, T.P. and A. J. Steckl*. "Plasma Etching of Refractory Gates for VLSI Applications." *J. Electrochem. Soc.* (Vol. 131, No. 10). October 1984. pp. 2325-2335.

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Chung, C.W. and H.G. Song*. "Study on Fence-Free Platinum Etching Using Chlorine-Based Gases in Inductively Coupled Plasma." *J. Electrochem. Soc.* (Vol. 144, No. 11). November 1997. pp. L294-L296.

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Ye, Yan**. "0.35-Micron and Sub-0.35-Micron Metal Stack Etch in a DPS Chamber-DPS Chamber and Process Characterization." *Electrochem. Soc. Proc.* (Vol. 96-12). 1996. pp. 222-233.

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